MITSUBISHI ELECTRIC

< C band internally matched power GaAs FET >

MGFC41V6472

6.4 – 7.2 GHz BAND / 12W

DESCRIPTION

The MGFC41V6472 is an internally impedance-matched GaAs power FET especially designed for use in 6.4 – 7.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation
Internally matched to 50(ohm) system
- High output power
  P1dB=12W (TYP.) @f=6.4 – 7.2GHz
- High power gain
  GLP=9.0dB (TYP.) @f=6.4 – 7.2GHz
- High power added efficiency
  P.A.E.=32% (TYP.) @f=6.4 – 7.2GHz
- Low distortion [item -51]
  IM3=-45dBc (TYP.) @Po=30dBm S.C.L

APPLICATION

- item 01 : 6.4 – 7.2 GHz band power amplifier
- item 51 : 6.4 – 7.2 GHz band digital radio communication

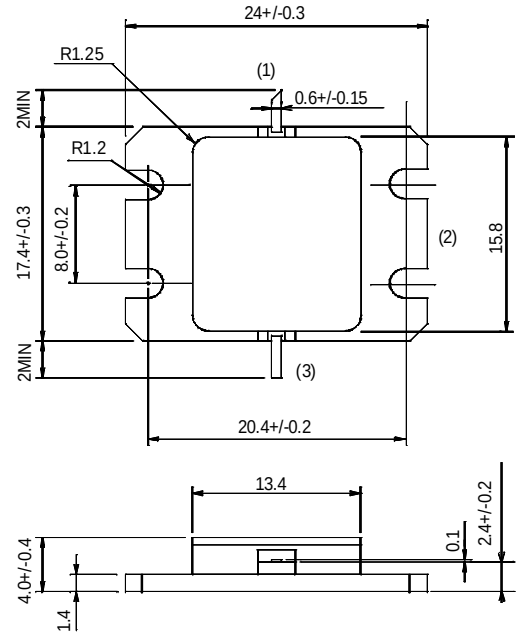
QUALITY

- IG

RECOMMENDED BIAS CONDITIONS

- VDS=10V • ID=3.4A Refer to Bias Procedure • RG=50ohm

OUTLINE DRAWING Unit: millimeters (inches)



(1): GATE
(2): SOURCE (FLANGE)
(3): DRAIN

GF-18

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	12	A
IGR	Reverse gate current	-30	mA
IGF	Forward gate current	63	mA
PT *1	Total power dissipation	53.6	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

*1 : Tc=25°C

Keep Safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable , but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury , fire or property damage. Remember to give due consideration to safety when making your circuit designs , with appropriate measure such as (I) placement of substitutive , auxiliary circuits , (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	-	12	A
gm	Transconductance	VDS=3V,ID=3.0A	-	3	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=30mA	-	-	-5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=3.4A	40	41	-	dBm
GLP	Linear Power Gain	f=6.4 – 7.2GHz	8	9	-	dB
ID	Drain current		-	-	-	A
P.A.E.	Power added efficiency		-	32	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	2.2	2.8	°C/W

*2 :item -51 ,2 tone test,Po=30dBm Single Carrier Level ,f=7.2GHz,delta f=10MHz
*3 :Channel-case

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